

# Leo J Schowalter

## List of Publications by Year in descending order

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Version: 2024-02-01

18  
papers

1,729  
citations

516561

16  
h-index

839398

18  
g-index

18  
all docs

18  
docs citations

18  
times ranked

1361  
citing authors

#	ARTICLE	IF	CITATIONS
1	Continuous-wave lasing of AlGaIn-based ultraviolet laser diode at 274.8 nm by current injection. Applied Physics Express, 2022, 15, 041007.	1.1	25
2	MBE growth and donor doping of coherent ultrawide bandgap AlGaIn alloy layers on single-crystal AlN substrates. Applied Physics Letters, 2021, 118, .	1.5	16
3	Impact of heat treatment process on threshold current density in AlGaIn-based deep-ultraviolet laser diodes on AlN substrate. Applied Physics Express, 2021, 14, 051003.	1.1	9
4	Improve efficiency and long lifetime UVC LEDs with wavelengths between 230 and 237 nm. Applied Physics Express, 2020, 13, 022001.	1.1	47
5	Space charge profile study of AlGaIn-based p-type distributed polarization doped claddings without impurity doping for UV-C laser diodes. Applied Physics Letters, 2020, 117, .	1.5	26
6	The 2020 UV emitter roadmap. Journal Physics D: Applied Physics, 2020, 53, 503001.	1.3	289
7	Molecular beam homoepitaxy on bulk AlN enabled by aluminum-assisted surface cleaning. Applied Physics Letters, 2020, 116, .	1.5	26
8	On-wafer fabrication of etched-mirror UV-C laser diodes with the ALD-deposited DBR. Applied Physics Letters, 2020, 116, .	1.5	42
9	Surface control and MBE growth diagram for homoepitaxy on single-crystal AlN substrates. Applied Physics Letters, 2020, 116, .	1.5	26
10	Design and characterization of a low-optical-loss UV-C laser diode. Japanese Journal of Applied Physics, 2020, 59, 094001.	0.8	31
11	A 271.8 nm deep-ultraviolet laser diode for room temperature operation. Applied Physics Express, 2019, 12, 124003.	1.1	217
12	AlGaIn Light-Emitting Diodes on AlN Substrates Emitting at 230 nm. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700660.	0.8	29
13	270 nm Pseudomorphic Ultraviolet Light-Emitting Diodes with Over 60 mW Continuous Wave Output Power. Applied Physics Express, 2013, 6, 032101.	1.1	153
14	High Output Power from 260 nm Pseudomorphic Ultraviolet Light-Emitting Diodes with Improved Thermal Performance. Applied Physics Express, 2011, 4, 082101.	1.1	135
15	The progress of AlN bulk growth and epitaxy for electronic applications. Physica Status Solidi (A) Applications and Materials Science, 2009, 206, 1153-1159.	0.8	51
16	Large-area AlN substrates for electronic applications: An industrial perspective. Journal of Crystal Growth, 2008, 310, 4020-4026.	0.7	113
17	Ultraviolet semiconductor laser diodes on bulk AlN. Journal of Applied Physics, 2007, 101, 123103.	1.1	144
18	Some effects of oxygen impurities on AlN and GaN. Journal of Crystal Growth, 2002, 246, 287-298.	0.7	350